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(54) **SEMICONDUCTOR DEVICE, METHOD FOR MANUFACTURING SEMICONDUCTOR DEVICE, AND ELECTRONIC DEVICE**

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(57) **ABSTRACT**

A semiconductor device includes a channel layer configured to include a first nitride semiconductor containing gallium (Ga) and a first crystal dislocation density, and a barrier layer provided over a first surface side of the channel layer, and configured to include a second nitride semiconductor containing aluminum (Al) and a second crystal dislocation density, wherein the second crystal dislocation density is larger than the first crystal dislocation density.